**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

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| APPLICANT: | Lea Di Cioccio | CONFIRMATION No.: | 5805 |
| SERIAL NO.: | 10/526,657 | ART UNIT: | 2822 |
| FILING DATE: | March 2, 2005 | EXAMINER: | Barnes, Seth W. |

TITLE: SiCOI TYPE COMPOSITE SUBSTRATE MANUFACTURING METHOD COMPRISING AN EPITAXY STEP

**Mail Stop Amendment**
**Commissioner for Patents**
**P.O. Box 1450**
**Alexandria, VA 22313-1450**

## STATEMENT OF THE SUBSTANCE OF THE INTERVIEW

Dear Sir:

This is a Statement of the Substance of the Interview conducted on November 7, 2007 between Examiner Barnes and Applicant's representative Michael Fainberg (Reg. No. 50,441). The statement is timely submitted within one month from the mailing date of the Interview Summary Form dated November 28, 2007.

During the Interview, the Examiner and the Applicant's representative discussed the Office Action dated May 18, 2007 and, in particular, the rejection of claim 7 over Letertre publication. The Applicant's representative traversed the rejection of claim 7 on the grounds that Letertre fails to disclose all limitation of the claim and, in particular, a method for manufacturing SiCOI substrate comprising the steps of "supplying an initial substrate comprising a SiC support bearing a layer of $SiO_2$ whereon a thin layer of SiC is transferred" and "conducting an epitaxy of SiC on the thin layer of SiC at a temperature from 1450°C to 1550°C," as recited in claim 7.

More specifically, the Applicant's representative asserted that Letertre does not disclose $SiO_2$ as a bonding layer between SiC substrate and the thin layer of SiC. Even though Letertre mentions that it is known to use oxide layer as a bonding layer between SiC substrate and thin SiC film (see page 151), Letertre does not disclose that such oxide layer may be Silicon Oxide ($SiO_2$) as recited in claim 7 of the present application. Moreover, in the same paragraph, Letertre propose a new method for fabricating SiCOI substrate, which does not involve oxide as the bonding layer, thereby teaching away from the claimed invention. In contrast, Letertre discloses use of tungsten silicide ($WSi_2$) as a preferred bonding agent.

Furthermore, Applicant's representative submitted that Letertre fails to describe epitaxy of SiC on the thin layer of SiC, which are bonded using $SiO_2$, at a temperature from 1450°C to 1550°C, which is an unexpected result of the method recited in claim 7.

At least for these reasons, the present application is believed to be allowable.

Applicant respectfully requests entry of the above statement of the substance of the interview into the record of the present application.

Respectfully submitted,

Dated: December 28, 2007

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